

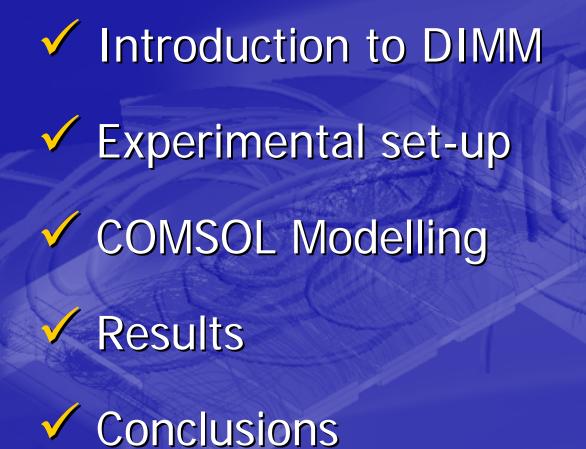
Numerical and Experimental Analysis of Natural and Mixed Convection Heat Transfer for Vertically Arranged DIMM

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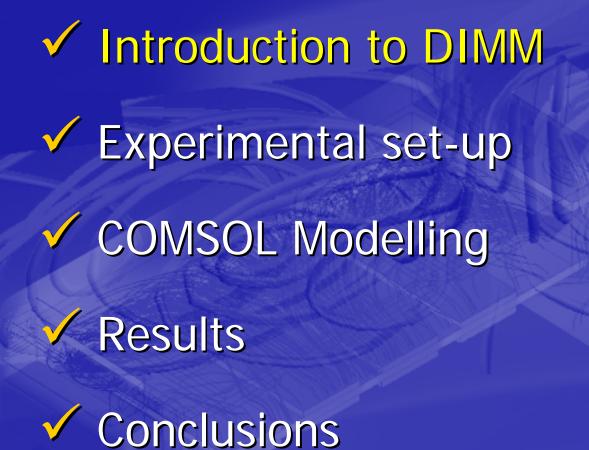














Electronic devices produce a very important rate of specific heat as a by-product of their normal operation.

Among the high power components, Random Access Memory modules are one of the more sensitive thermal subsystem of an assembled computer.

Cooling of those devices is always performed by mechanical ventilation systems.

However, the forced air flow is often disturbed by many factors. Cables, drive bays and brackets can determinate bypass over the memory components, forcing the subsystem to operate in mixed or natural convection conditions.





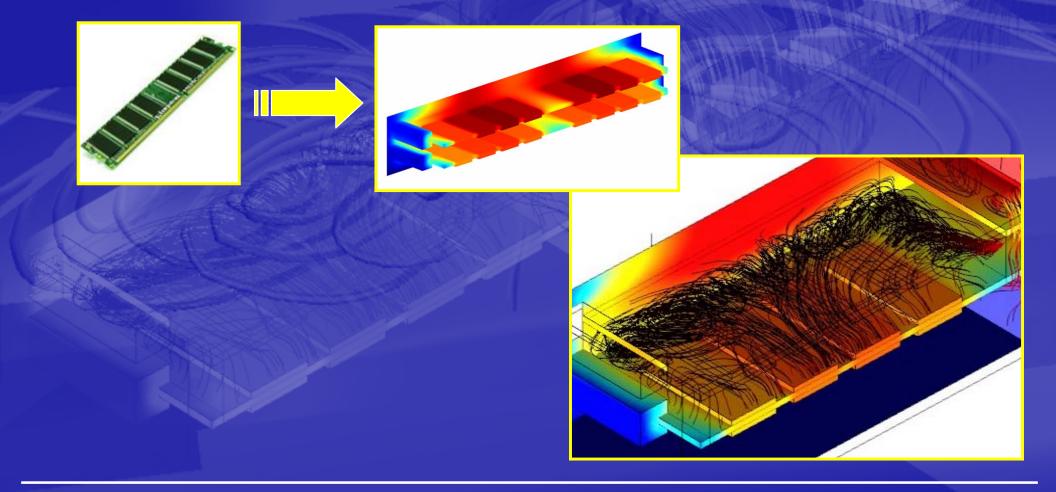
The actually most used memory in desktop Personal Computers is DIMM (Dual In-line Memory Module):

- 4-16 chip of synchrony dynamical memory with random access (SDRAM) type DDR [Vdd=2,5 V] (Double-Data Rate) o DDR2 [Vdd=1,8 V]
- Very small (135x30x1,3 mm) Printed Circuit Board (PCB)
- 184 different PIN on both faces of the PCB
- It is connected to the mainboard by a specific socket
- It is object of JEDEC (Joint Electron Device Engineering Council) standards

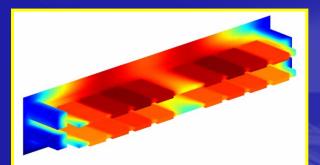
In order to guarantee the reliability of these systems, it is strictly necessary that the memory chip does not over, during its functioning, the maximum temperature recommended in the technical documentations of constructors (Micron Technology, 80-110°C).



For predictive estimation of operative temperature of DIMM modules, leading constructors (Micron, Infineon, ...) recommend CFD modelling







The numerical model (and so the results carriedout by simulations) is reliable ?

It is always advisable firstly testing its reliability.

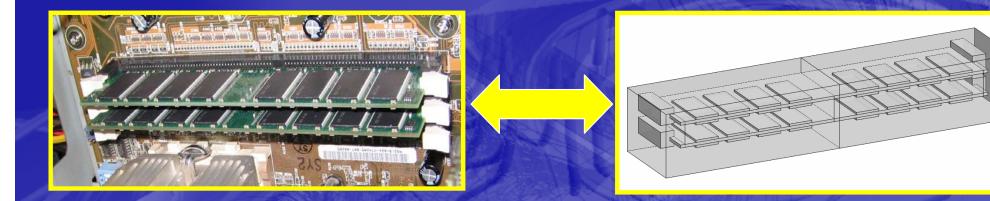
One suitable way to proceed consists in:

- > setting-up an experimental apparatus reproducing a test section
- conducing test experiments on this set-up

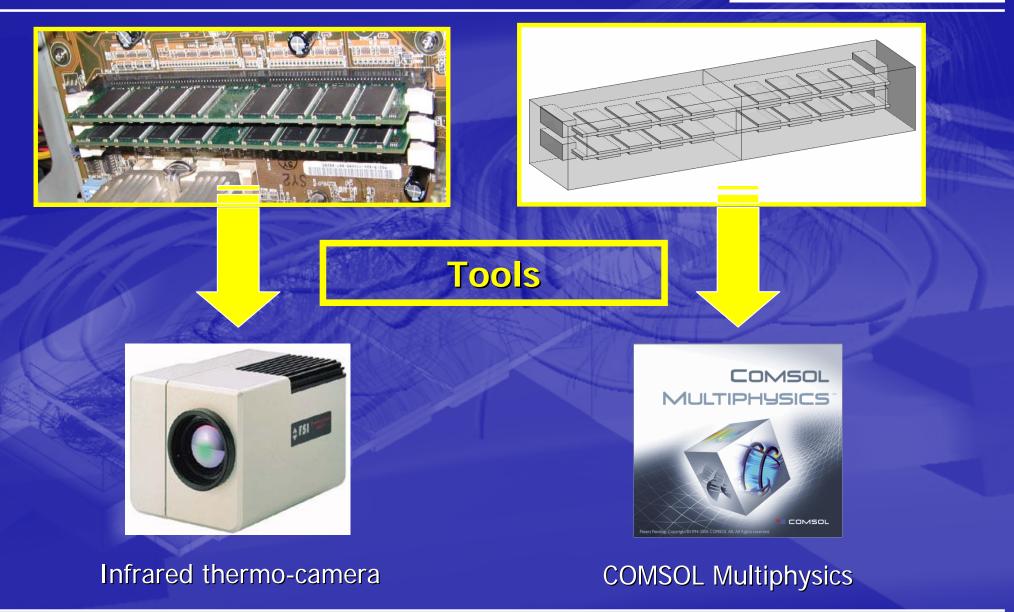
some data become available to be compared with those obtained by using the numerical model



The aim of this study has been comparing experimental and numerical results concerning thermal levels of operating DIMM

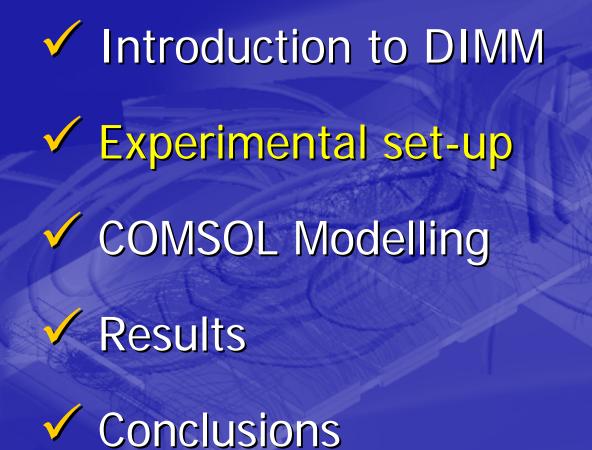














The experimental technique chosen to produce comparing data for numerical results lies on a thermo-graphic investigation on surfaces thermal distribution of Dual In-line Memory Modules during operative conditions.

#### The experimental apparatus mainly consists in:

➤ a test PC where two 16-chip memory modules (DDR - 512 MB - 266 MHz) were arranged on

> an infrared camera (ThermaCAM Flir SC 3000) for detection of surface thermal fields



➤ a laptop PC used for acquisition



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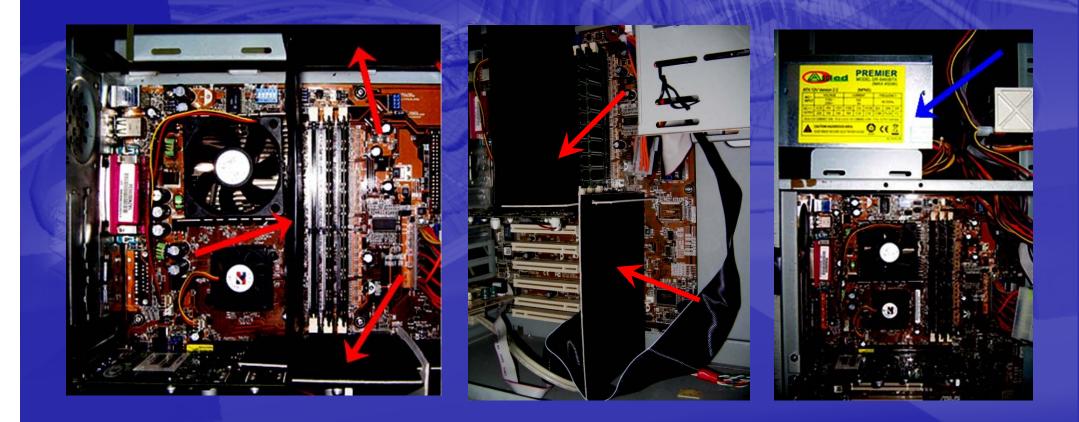
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➤ a laptop PC used for acquisition





In order to reproduce the most critical heat transfer condition of functioning for the electronic devices, some black panels (red arrows) were employed in order to shield the memory modules by the forced air-flow produced by ventilators. The power-pack was put outside the case (blue arrow).





Frontal black box built around the DIMM also resulted helpful for thermographical acquisition.



➢ Hot electronic components mounted on the mainboard were hindered by the black panels, allowing to set temperature range of the acquisition system with thermal values characteristic of the DIMM.



During experimental running specific applications were launched on the test PC in order to load memories by a known electrical power (0.3-0.4 [W]).

The experimental acquisitions were recorded each 5 seconds, during a transient time of 3-4 hours.

Exceeded this time a stationary thermal behaviour was reached by the dissipating components

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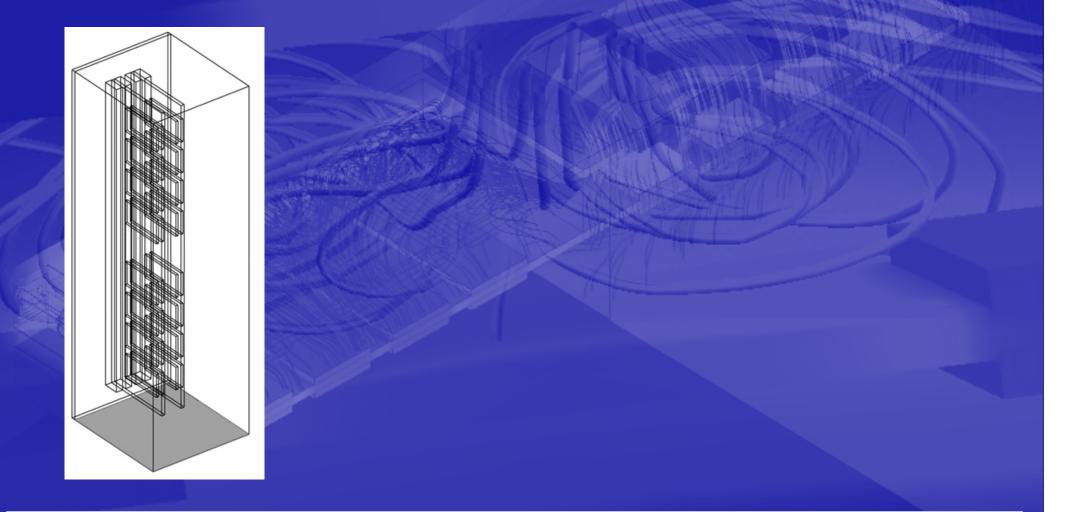




Introduction to DIMM Experimental set-up ✓ COMSOL Modelling Results Conclusions

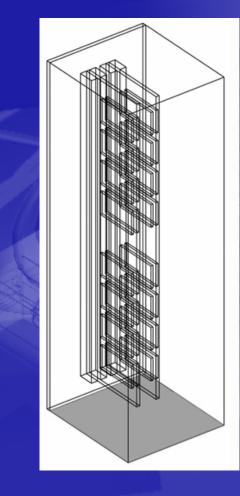


The considered physical system is outlined by parallel boards (Printed Circuit Board) surrounded by air and arranging on multiple heat sources (Chip)





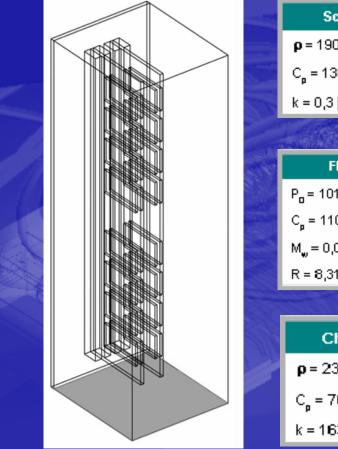
Governing equations for solving thermal and dynamical fields read as:

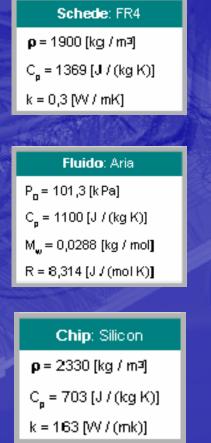


 $\rho \frac{D\vec{v}}{D\tau} = -\nabla p + \vec{F} + \mu \nabla^2 \vec{v}$  $\frac{\partial \rho}{\partial \tau} + \nabla \cdot \left( \rho \vec{v} \right) = 0$  $\rho C_P \frac{DT}{D\tau} = \nabla \cdot \left(\lambda \nabla \cdot T\right) + q$ 



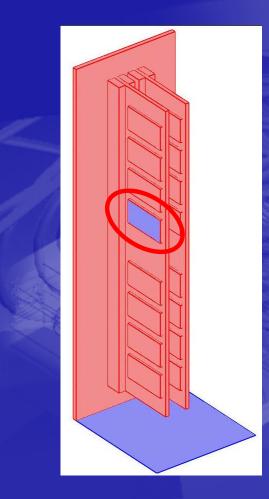
The energy equation is solved in fluid as well as in solid sub-domains of system, by considering appropriate values for thermal conductivity







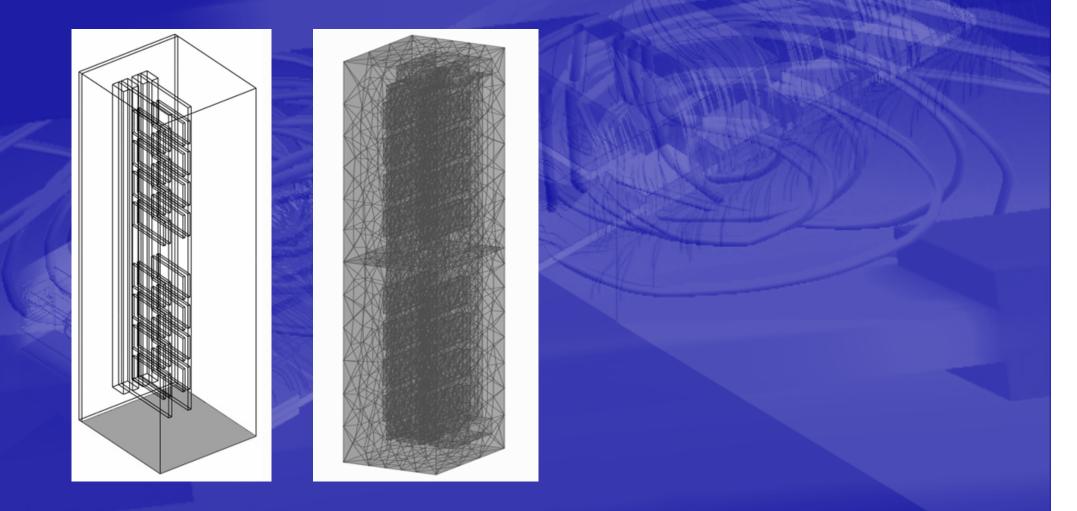
#### Only in chip sub-domains the heat source term is different from zero



P(PRE_PDN)	4.8mW
P(PRE_STBY)	12.0mW
P(ACT_PDN)	9.7mW
P(ACT_STBY)	26.4mW
P(REF)	4.6mW
Total Background Power	57.6mW
P(ACT)	20.7mW
Total Activate Power	20.7mW
P(WR)	9.6mW
P(RD)	20.0mW
P(DQ)	6.2mW
Total Read/Write Power	25.omW
Total DDR1 SDRAM Power	114.1mW
P(PRE_PDN)	2.0mW
P(PRE_STBY)	30.0mW
P(ACT_PDN)	0.0mW
P(ACT_STBY)	105.2mW
P(REF)	5.0mW
Total Background Power	142.2mW
P(ACT)	74.6mW
Total Activate Power	74.6mW
P(WR)	46.9mW
P(RD)	97.6mW
P(DQ)	18.6mW
Total Read/Write Power	103.2MW

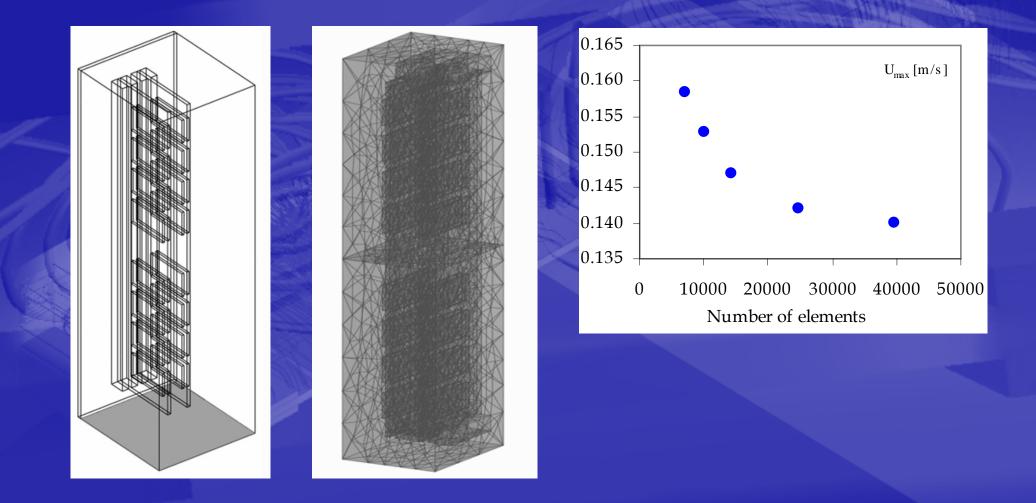


Spatial discretization of differential operators made on no-structured and nouniform mesh



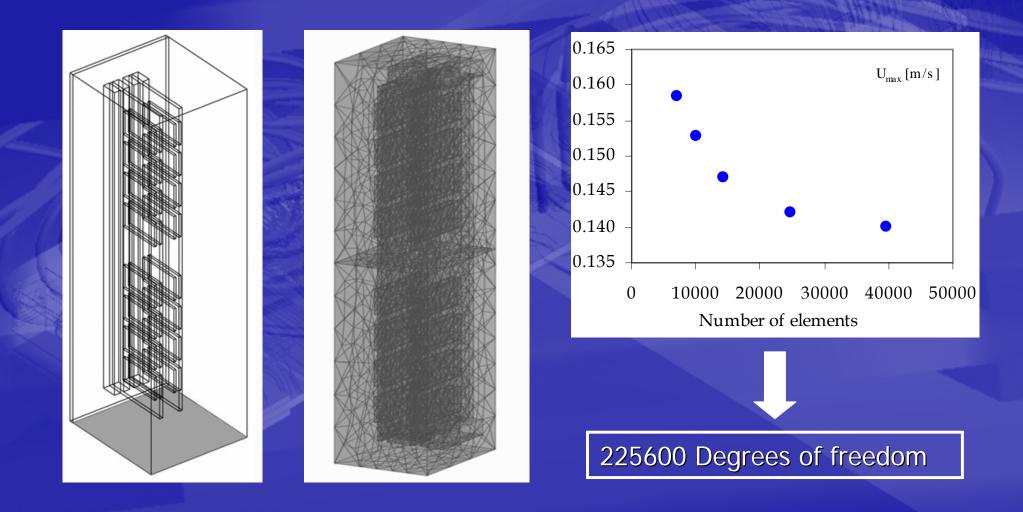


Influence of computational grid has been preliminary studied in order to assure mesh-independent results



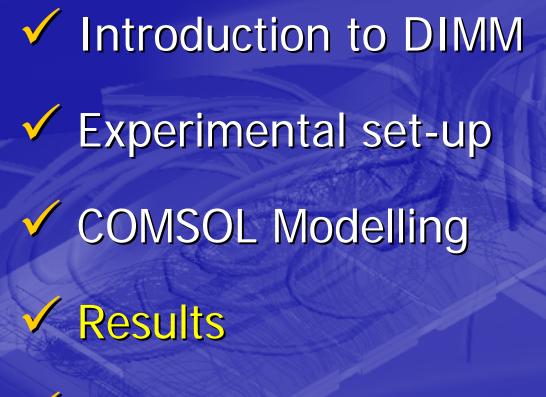


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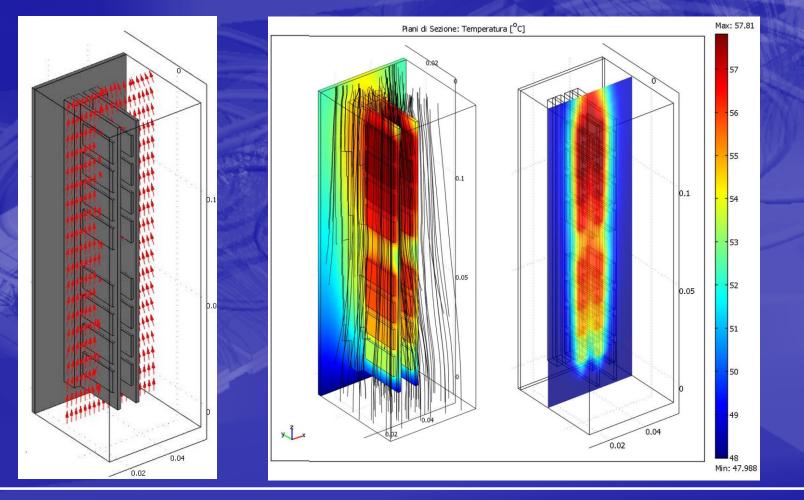






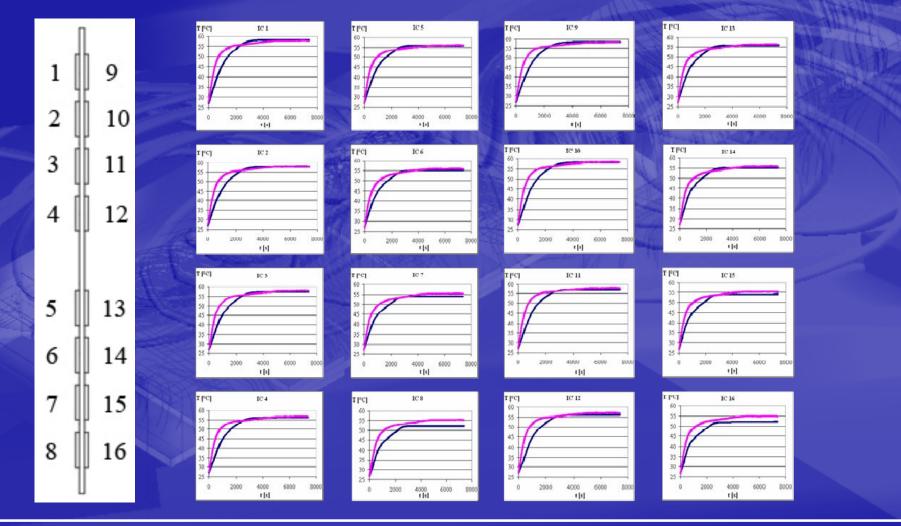


Fluid is propelled by buoyancy force to flow up. Heat is vertically transported. The integrated circuits arranged in the top portion of the modules manifest higher thermal levels



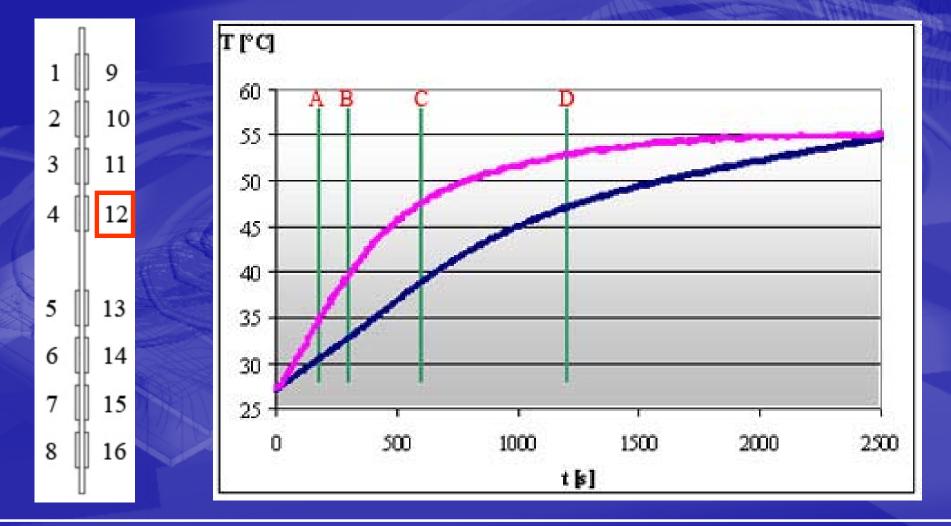


Transient analysis: comparison of time evolution of experimental (magenta lines) and numerical (blue lines) chips mean temperature

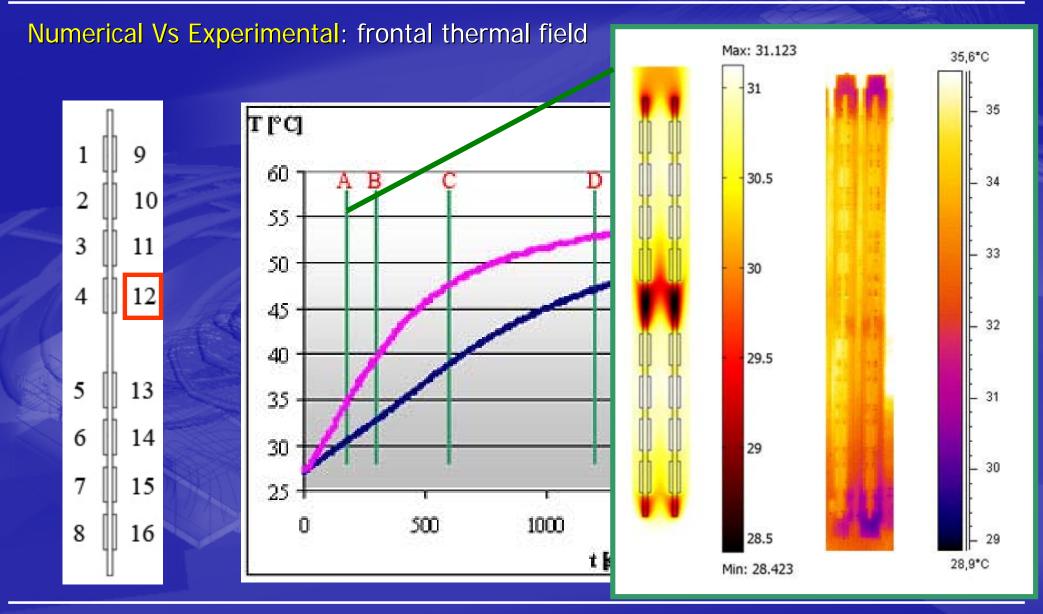




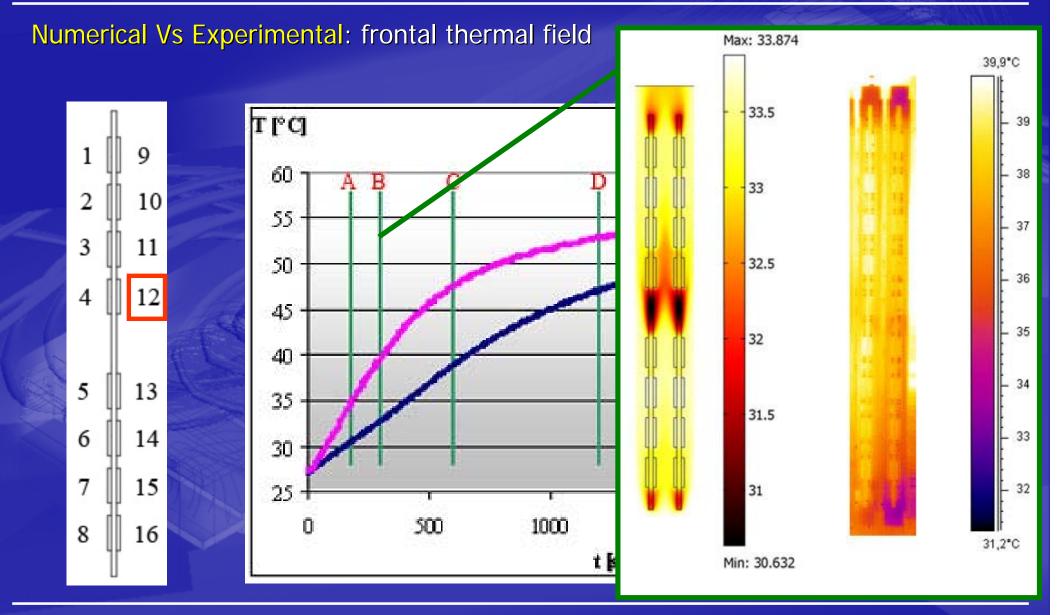
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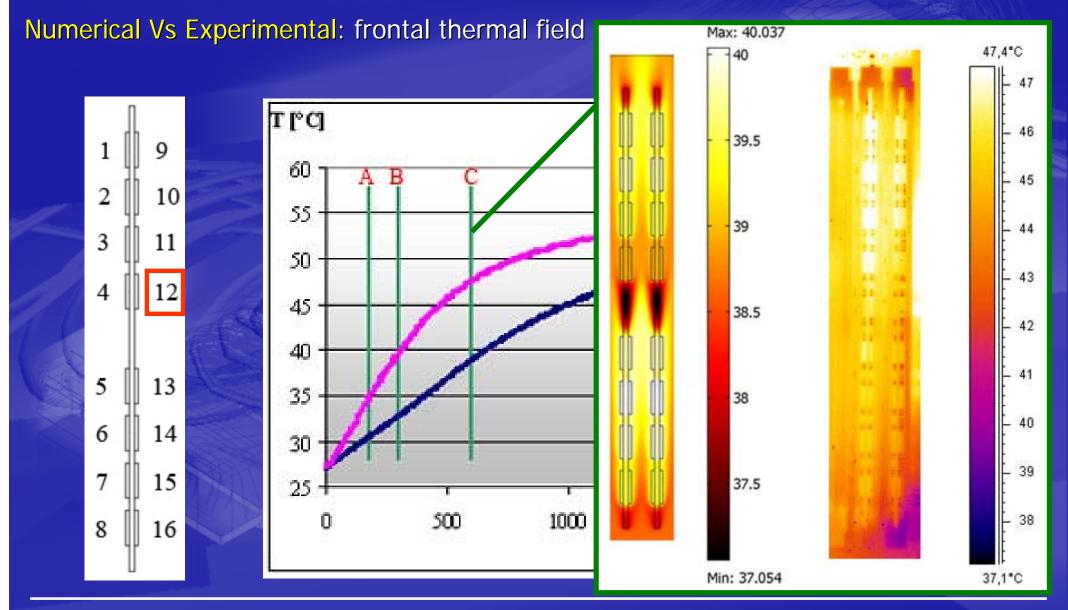






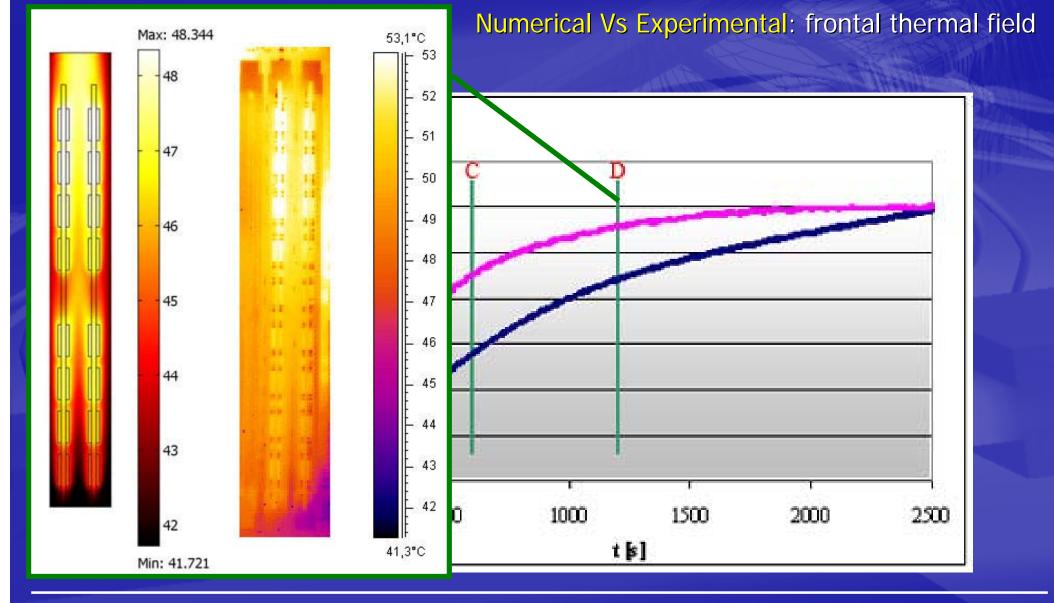






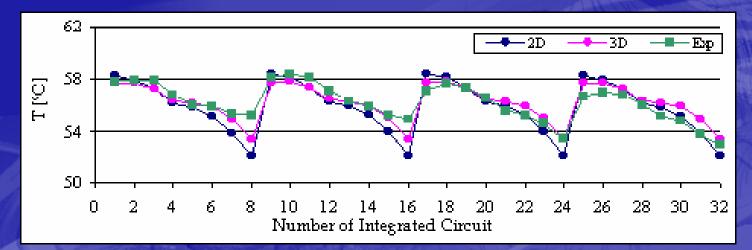
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Steady solution: comparison of experimental and numerical chips mean temperature



IC	Num	Exp	(Num-Exp)/Exp %
1	57.66	57.80	0.24
2	57.72	57.95	0.40
3	57.25	57.88	1.09
4	56.38	56.74	0.63
5	56.14	55.96	0.32
6	55.84	55.86	0.04
7	54.92	55.33	0.74
8	53.34	55.26	3.47



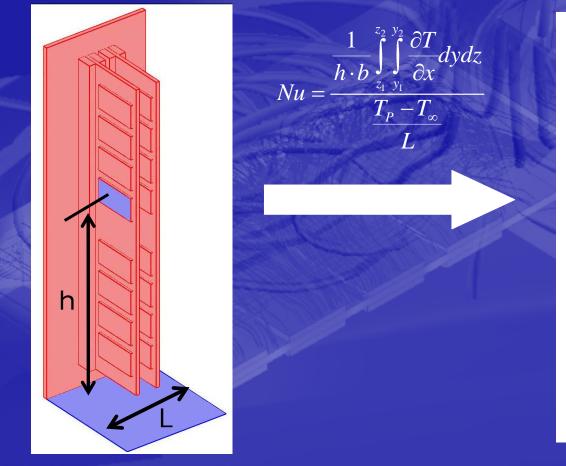


Models considering imposed air flow rate coming from the bottom surface of the outlined air volume have been built





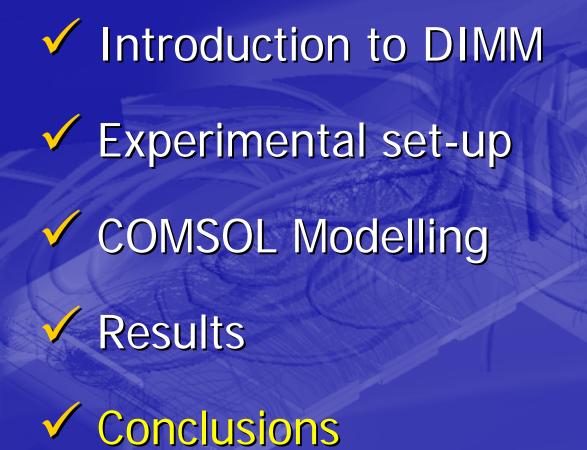
Convective heat transfer coefficient have been computed Natural and mixed convective heat transfer coefficients have been compared



IC	$\frac{T_{nat} - T_{v=0.1}}{T_{nat}}\%$	$\frac{T_{nat} - T_{v=0.2}}{T}$	$\frac{Nu_{v=0.1} - Nu_{nat}}{Nu_{nat}}\%$	$\frac{Nu_{v=0.2} - Nu_{nat}}{Nu_{nat}}\%$
	1 nat	$T_{nat}$	1 VV nat	1 ver nat
1	1.59	3.25	12.52	32.32
2	1.68	3.34	13.52	35.54
3	1.75	3.59	15.59	39.81
4	1.83	3.89	20.48	48.80
5	2.53	5.27	25.79	47.04
6	3.20	5.81	26.76	47.38
7	3.89	5.86	30.20	54.42
8	4.02	5.30	50.81	85.19
9	1.58	3.23	17.42	34.74
10	1.67	3.38	26.84	53.77
11	1.73	3.56	34.96	70.68
12	1.81	3.86	45.88	115.72
13	2.52	5.24	80.97	228.95
14	3.24	5.93	101.31	291.41
15	3.99	6.06	192.06	311.35
16	4.11	5.46	197.02	327.19









This study highlights the opportunity to exploit a numerical approach in order to simulate thermal and fluid-dynamical behaviour of electronic devices.

The paper otherwise underlines the unquestionable importance of a validation step for the numerical model, strictly needed in order to assure effectiveness and reliability of the results carried-out

Comparison has been made between DIMM thermal fields experimentally detected and numerically computed

> Results show good agreement each other

The validated numerical model has been exploited in order to quantify heat transfer coefficients during several operating conditions

### THANK YOU !!!



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